BUK755R4-100E

N-channel TrenchMOS standard level FET

11 September 2012 | Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in a SOT78 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C

1.3 Applications

- 12V, 24V and 48V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	-	100	V
I_D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; Fig. 1	[1]	-	-	120	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 2		-	-	349	W
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 11		-	4.1	5.2	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	V_{GS} = 10 V; I_D = 25 A; V_{DS} = 80 V; T_j = 25 °C; Fig. 13; Fig. 14		-	65	-	nC

[1] Continuous current is limited by package.

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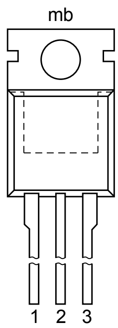
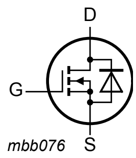
2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 TO-220AB (SOT78A)	
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK755R4-100E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78A

4. Marking

Table 4. Marking codes

Type number	Marking code
BUK755R4-100E	BUK755R4-100E

5. Limiting values

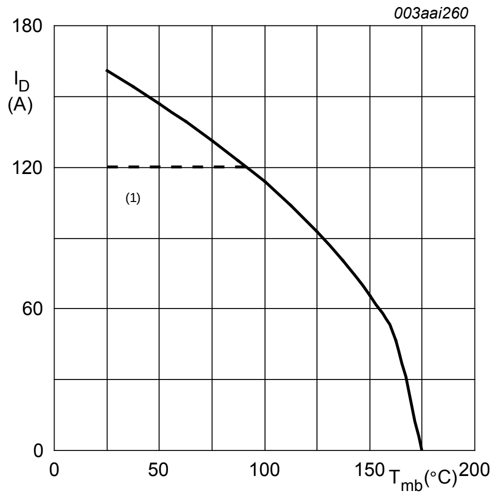
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	100	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20$ kΩ		-	100	V
V_{GS}	gate-source voltage	$T_j = 175$ °C; DC		-20	20	V
I_D	drain current	$T_{mb} = 25$ °C; $V_{GS} = 10$ V; Fig. 1	[1]	-	120	A
		$T_{mb} = 100$ °C; $V_{GS} = 10$ V; Fig. 1		-	112	A
I_{DM}	peak drain current	$T_{mb} = 25$ °C; pulsed; $t_p \leq 10$ µs; Fig. 4		-	631	A

Symbol	Parameter	Conditions		Min	Max	Unit
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 2		-	349	W
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
Source-drain diode						
I_S	source current	T_{mb} = 25 °C	[1]	-	120	A
I_{SM}	peak source current	pulsed; t_p ≤ 10 µs; T_{mb} = 25 °C		-	631	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 120 A; V_{sup} ≤ 100 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 3	[2][3]	-	387	mJ

[1] Continuous current is limited by package.
[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
[3] Refer to application note AN10273 for further information.



(1) Capped at 120A due to package

Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \geq 10V$$

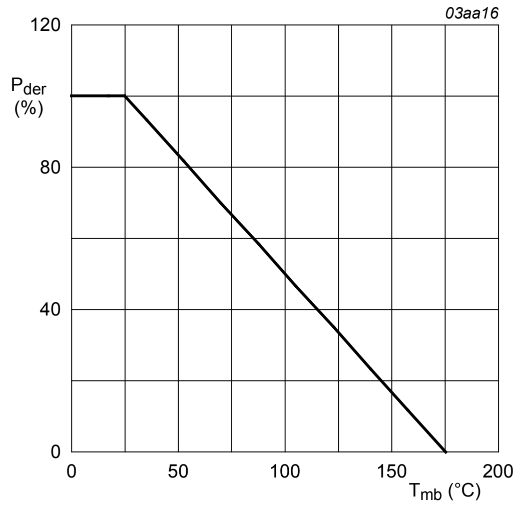


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

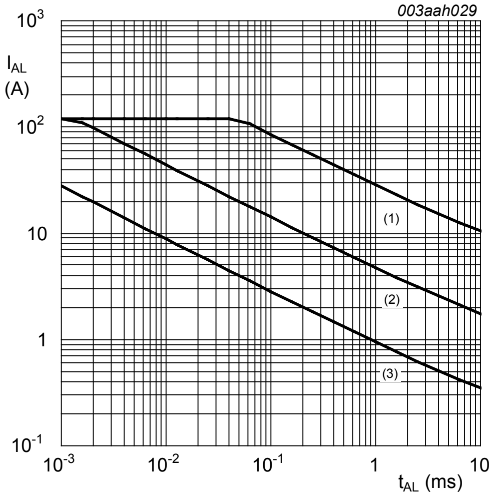


Fig. 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j\ (init)} = 25°C$; (2) $T_{j\ (init)} = 150°C$; (3) Repetitive Avalanche

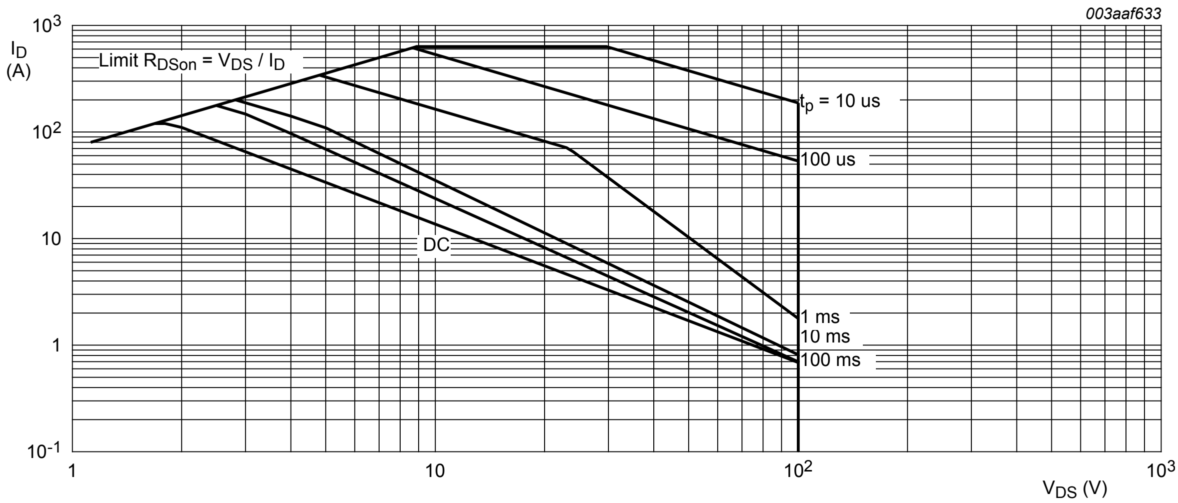


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25°C$; I_{DM} *is a single pulse*

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5		-	-	0.43	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in free air		-	60	-	K/W

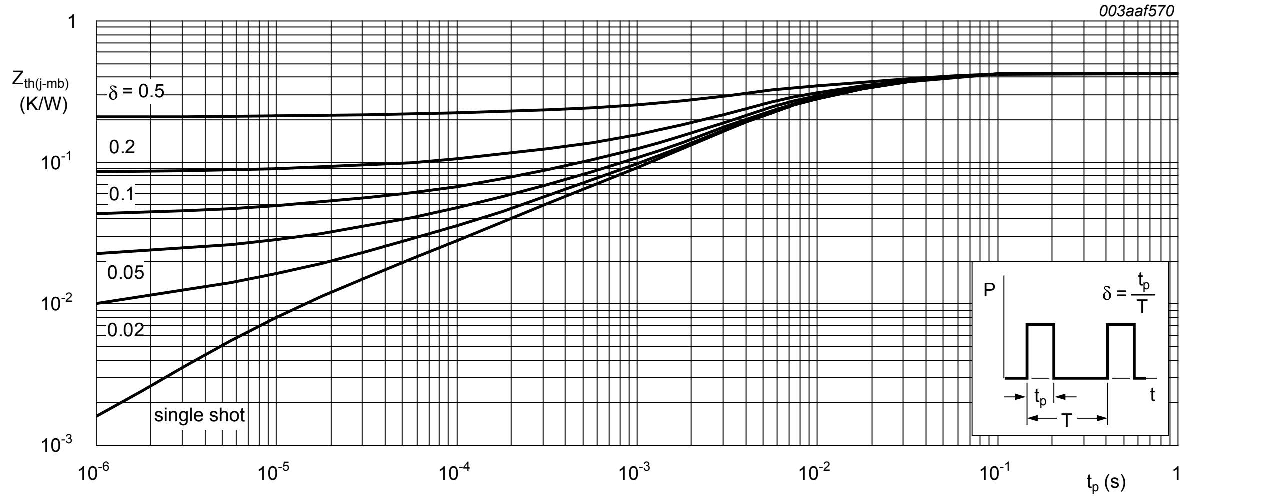


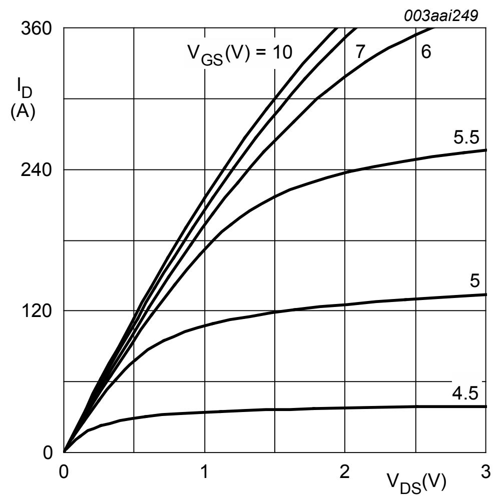
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration.

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		100	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C		90	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; Fig. 9; Fig. 10		2.4	3	4	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C; Fig. 9		1	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; Fig. 9		-	-	4.5	V
I_{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C		-	0.15	2	µA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C		-	-	500	µA
I_{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 11		-	4.1	5.2	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; Fig. 11; Fig. 12		-	-	14	mΩ
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	I_D = 25 A; V_{DS} = 80 V; V_{GS} = 10 V; T_j = 25 °C; Fig. 13; Fig. 14		-	180	-	nC
Q_{GS}	gate-source charge			-	34	-	nC
Q_{GD}	gate-drain charge			-	65	-	nC

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; T_j = 25 °C; Fig. 15		-	8860	11810	pF
C_{oss}	output capacitance			-	770	925	pF
C_{rss}	reverse transfer capacitance			-	546	750	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 80 V; R_L = 3.2 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 5 Ω		-	37	-	ns
t_r	rise time			-	62	-	ns
$t_{d(off)}$	turn-off delay time			-	158	-	ns
t_f	fall time			-	80	-	ns
L_D	internal drain inductance	from upper edge of drain mounting base to centre of die		-	2.5	-	nH
		from drain lead 6mm from package to centre of die		-	4.5	-	nH
L_S	internal source inductance	from source lead to source bond pad		-	7.5	-	nH
Source-drain diode							
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C; Fig. 16		-	0.77	1.2	V
t_{rr}	reverse recovery time	I_S = 20 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 25 V		-	65	-	ns
Q_r	recovered charge			-	191	-	nC



T_j = 25 °C; t_p = 300 µs

Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

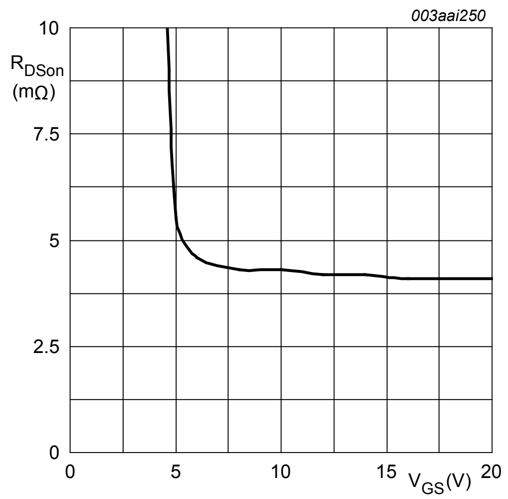


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25°C$; $I_D = 25A$

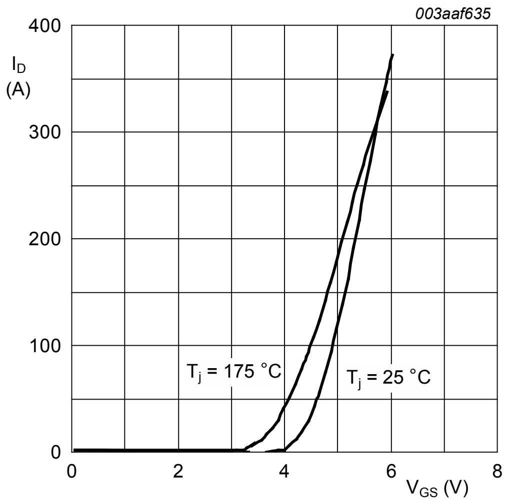


Fig. 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$V_{DS} = 12 V$

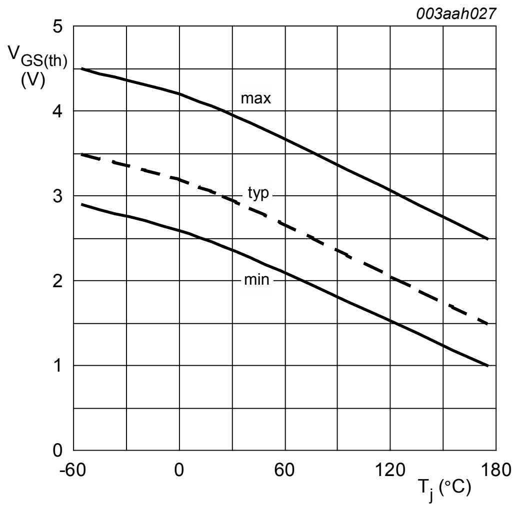


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$I_D = 1$ mA; $V_{DS} = V_{GS}$

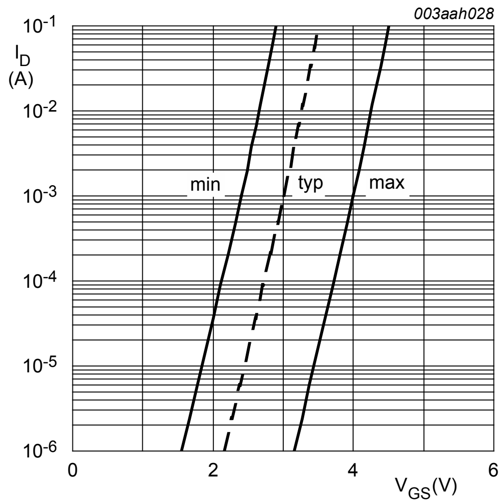
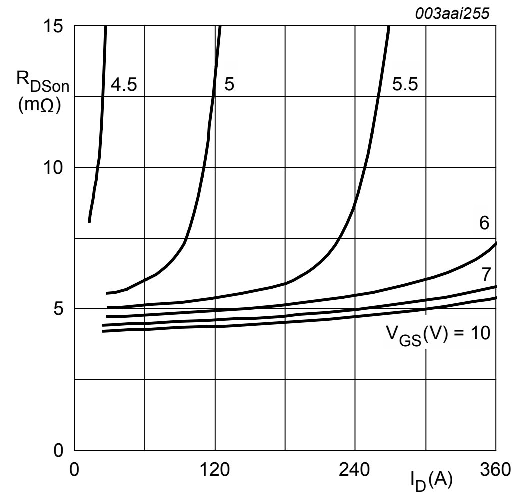


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25°C; \; V_{DS} = 5V$



T_j = 25 °C; t_p = 300 μs

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

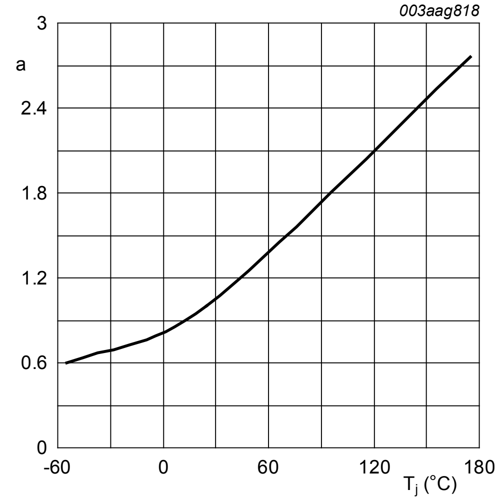
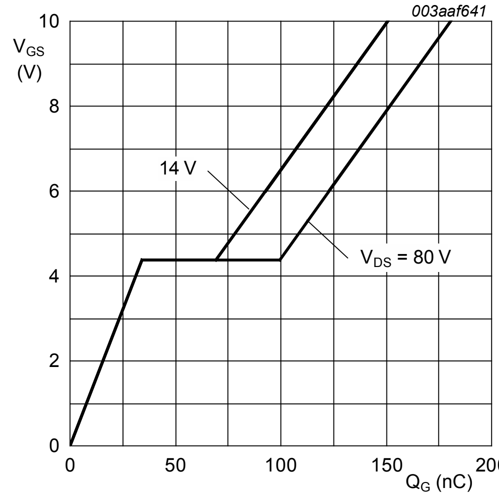


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25\,°C)}}$$



T_j = 25 °C; I_D = 25 A

Fig. 13. Gate-source voltage as a function of gate charge; typical values

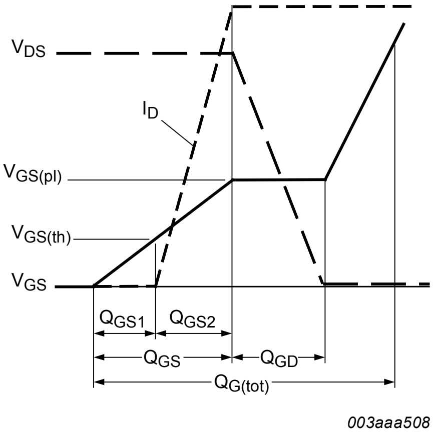
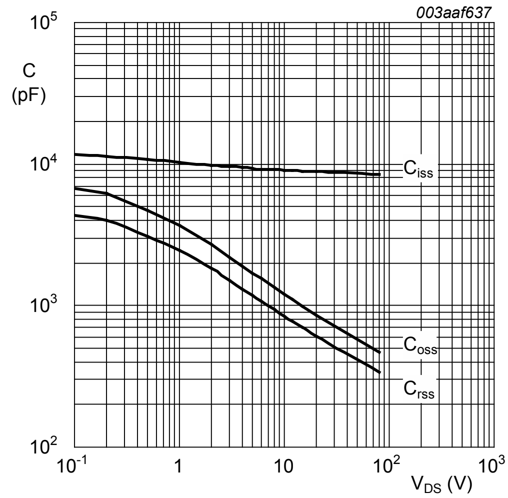
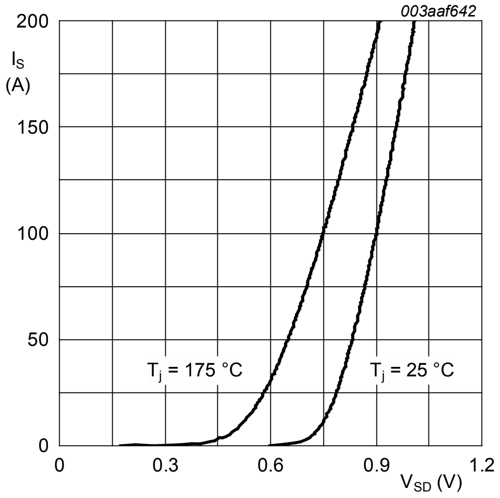


Fig. 14. Gate charge waveform definitions



V_{GS} = 0 V; f = 1 MHz

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

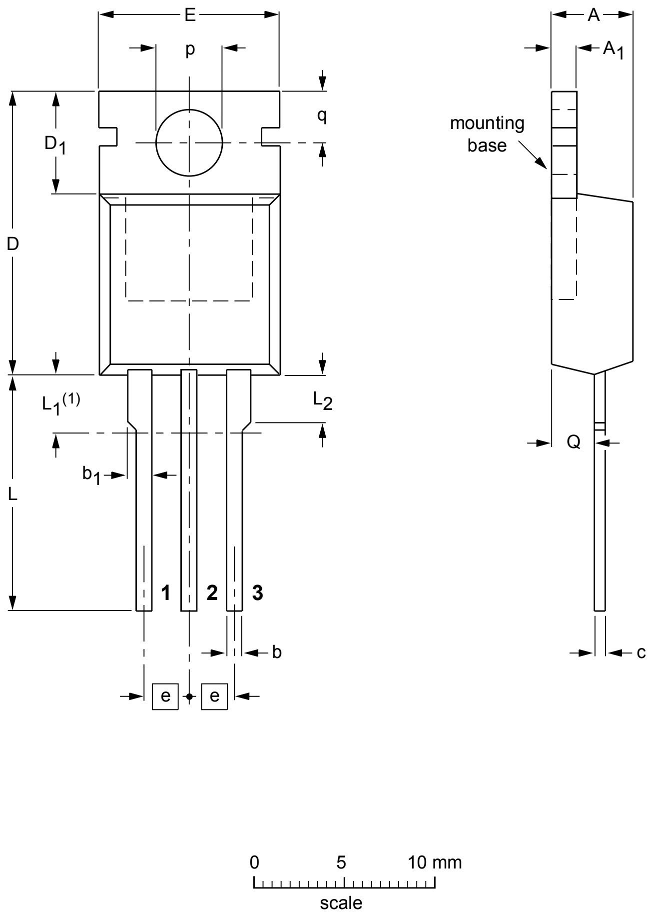


V_{GS} = 0 V

Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

8. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB **SOT78A**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	b_1	c	D	D_1	E	e	L	$L_1^{(1)}$	L_2 max.	p	q	Q
mm	4.5 4.1	1.39 1.27	0.9 0.6	1.3 1.0	0.7 0.4	15.8 15.2	6.4 5.9	10.3 9.7	2.54	15.0 13.5	3.30 2.79	3.0	3.8 3.6	3.0 2.7	2.6 2.2

Note

1. Terminals in this zone are not tinned.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78A		3-lead TO-220AB	SC-46			~~03-01-22~~ 05-03-14

Fig. 17. Package outline TO-220AB (SOT78A)

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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